

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSIII)

## 2SK3017

DC-DC Converter, Relay Drive and Motor Drive Applications

- Low drain-source ON resistance :  $R_{DS(ON)} = 1.05 \Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 7.0 S$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \mu A$  (max) ( $V_{DS} = 720 V$ )
- Enhancement mode :  $V_{th} = 2.0 \sim 4.0 V$  ( $V_{DS} = 10 V$ ,  $I_D = 1 mA$ )

### Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	900	V
Drain-gate voltage ( $R_{GS} = 20 k\Omega$ )	$V_{DGR}$	900	V
Gate-source voltage	$V_{GSS}$	$\pm 30$	V
Drain current	DC (Note 1)	$I_D$	8.5
	Pulse (Note 1)	$I_{DP}$	25.5
Drain power dissipation ( $T_c = 25^\circ C$ )	$P_D$	90	W
Single pulse avalanche energy (Note 2)	$E_{AS}$	966	mJ
Avalanche current	$I_{AR}$	8.5	A
Repetitive avalanche energy (Note 3)	$E_{AR}$	9	mJ
Channel temperature	$T_{ch}$	150	$^\circ C$
Storage temperature range	$T_{stg}$	$-55 \sim 150$	$^\circ C$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	1.39	$^\circ C / W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	41.6	$^\circ C / W$

Note 1: Ensure that the channel temperature does not exceed  $150^\circ C$ .

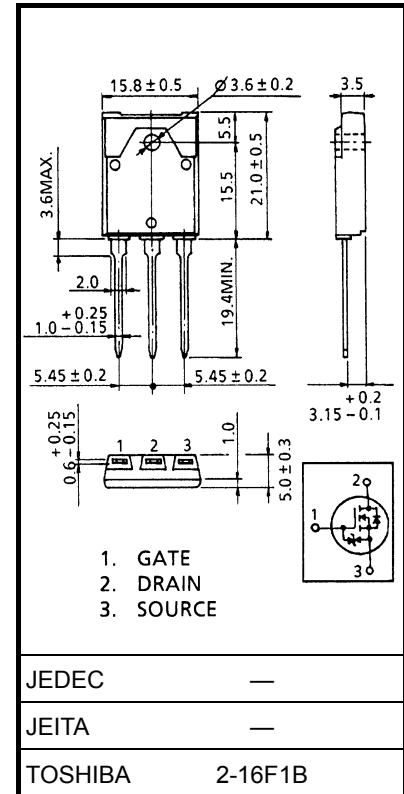
Note 2:  $V_{DD} = 90 V$ ,  $T_{ch} = 25^\circ C$  (initial),  $L = 24.5 mH$ ,  $R_G = 25 \Omega$ ,  $I_{AR} = 8.5 A$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.

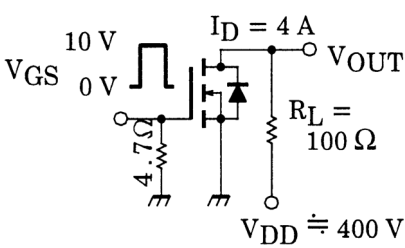
Please handle with caution.

Unit: mm



Weight: 5.8 g (typ.)

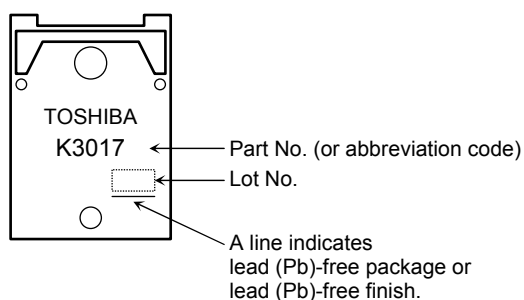
## Electrical Characteristics (Ta = 25°C)

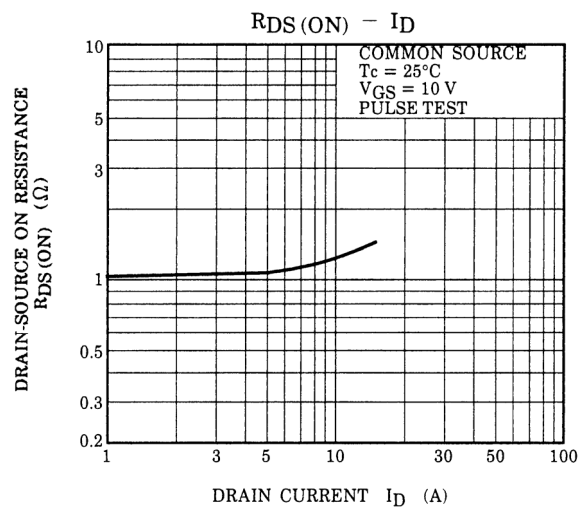
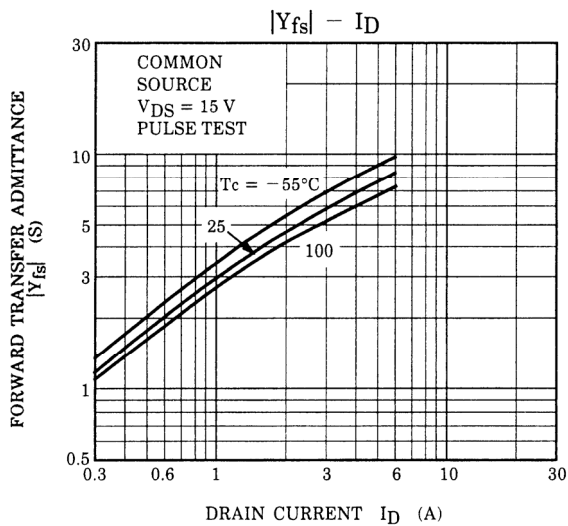
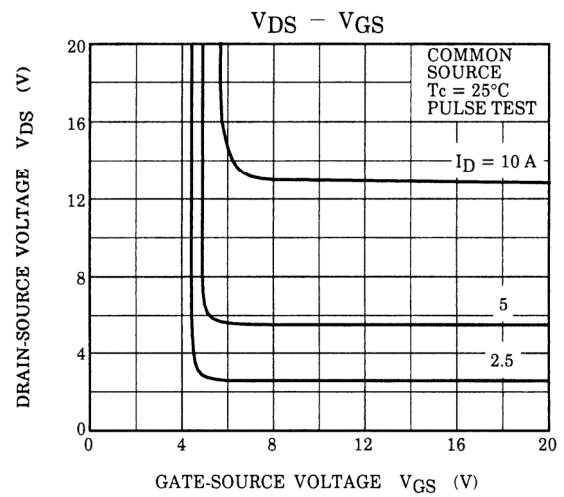
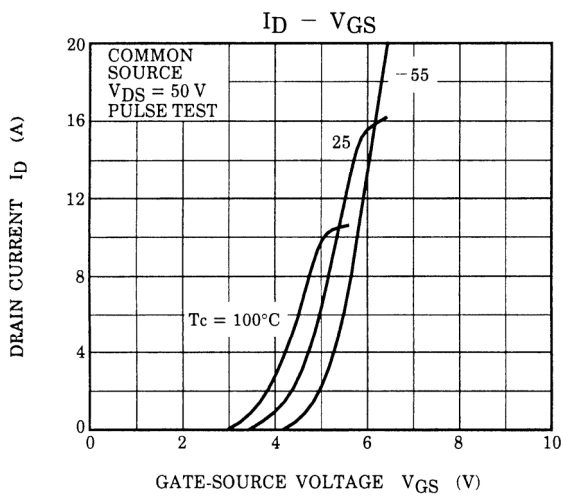
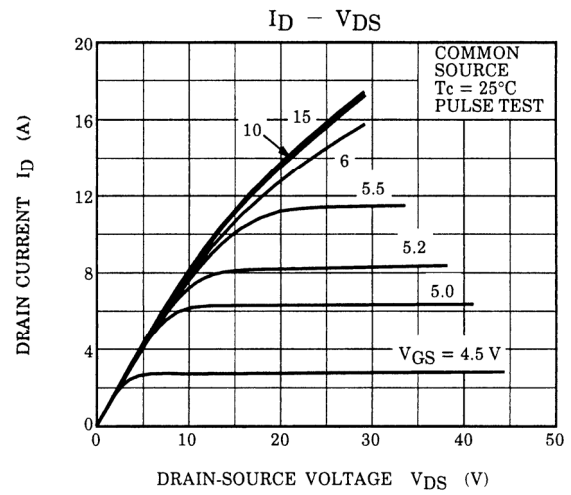
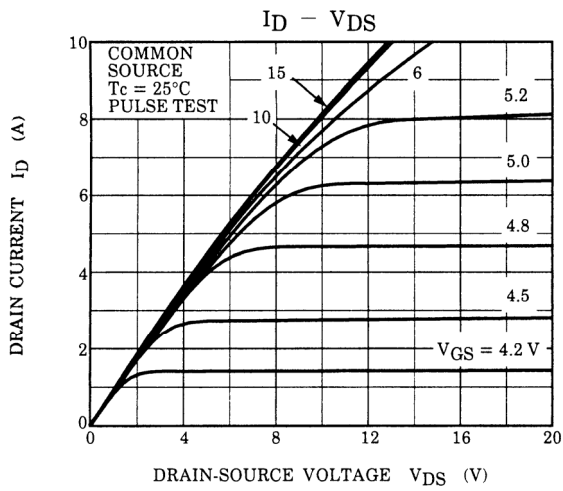
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 30 \text{ V}$ , $V_{DS} = 0 \text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Gate-source breakdown voltage		$V_{(BR) GSS}$	$I_G = \pm 10 \mu\text{A}$ , $V_{DS} = 0 \text{ V}$	$\pm 30$	—	—	V
Drain cut-off current		$I_{DSS}$	$V_{DS} = 720 \text{ V}$ , $V_{GS} = 0 \text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR) DSS}$	$I_D = 10 \text{ mA}$ , $V_{GS} = 0 \text{ V}$	900	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 4 \text{ A}$	—	1.05	1.25	$\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 15 \text{ V}$ , $I_D = 4 \text{ A}$	3.5	7.0	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 25 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$	—	2150	—	pF
Reverse transfer capacitance		$C_{rss}$		—	35	—	
Output capacitance		$C_{oss}$		—	220	—	
Switching time	Rise time	$t_r$	 <p><math>I_D = 4 \text{ A}</math> <math>V_{GS} = 10 \text{ V}</math> <math>V_{DS} = 400 \text{ V}</math> <math>R_L = 100 \Omega</math> <math>V_{DD} = 400 \text{ V}</math></p>	—	25	—	ns
	Turn-on time	$t_{on}$		—	60	—	
	Fall time	$t_f$		—	25	—	
	Turn-off time	$t_{off}$		—	120	—	
Total gate charge (Gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 400 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 8 \text{ A}$	—	70	—	nC
Gate-source charge		$Q_{gs}$		—	37	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	33	—	

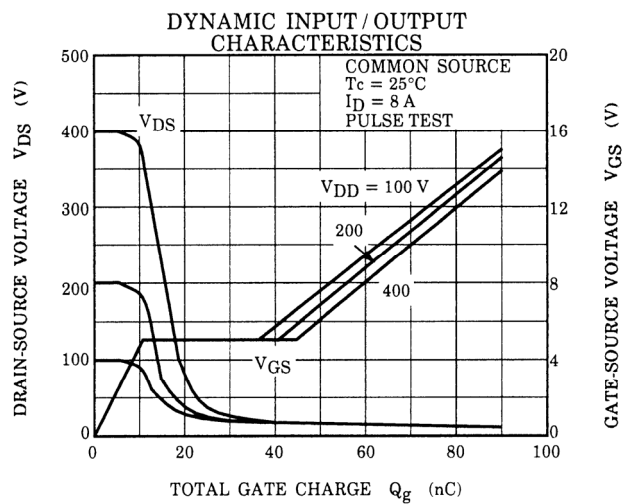
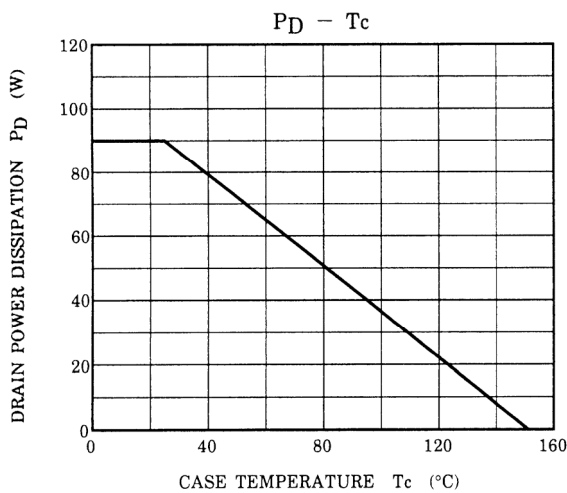
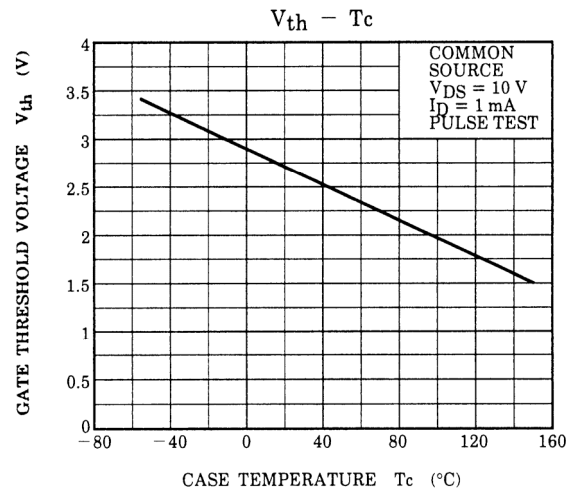
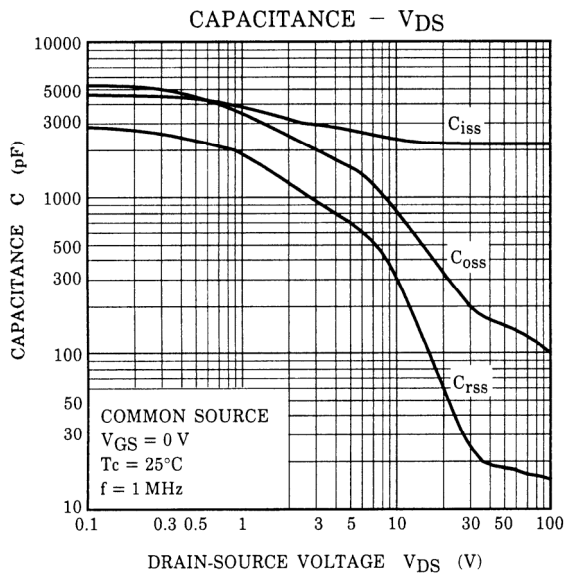
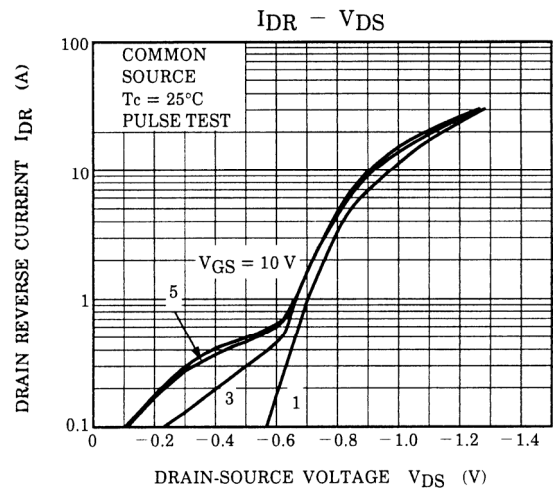
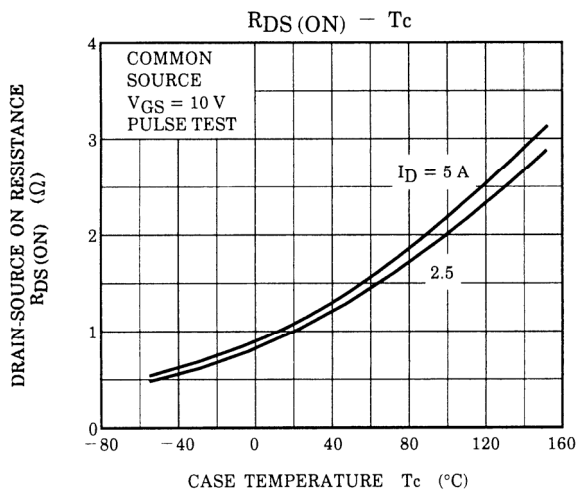
## Source-Drain Ratings and Characteristics (Ta = 25°C)

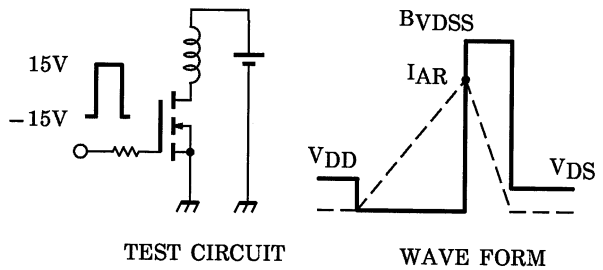
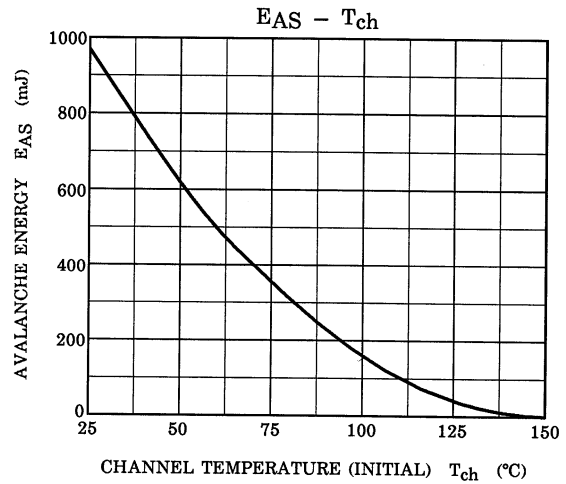
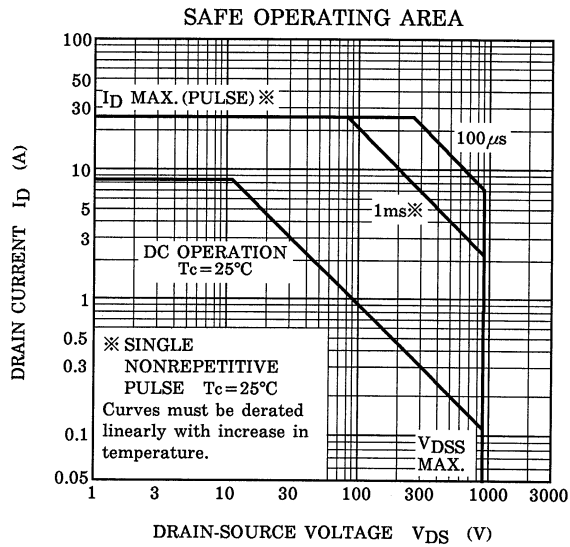
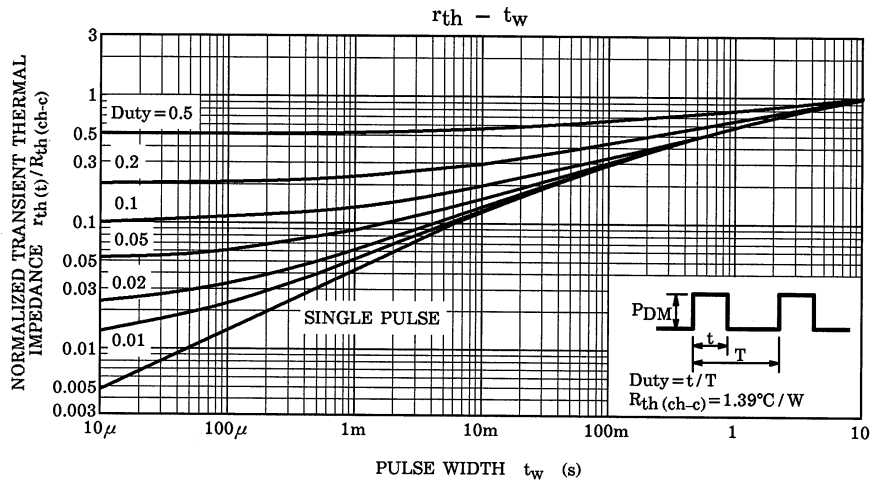
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	8.5	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	25.5	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 8.5 \text{ A}$ , $V_{GS} = 0 \text{ V}$	—	—	-1.9	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 8.5 \text{ A}$ , $V_{GS} = 0 \text{ V}$	—	1300	—	ns
Reverse recovery charge	$Q_{rr}$	$dI_{DR} / dt = 100 \text{ A} / \mu\text{s}$	—	14.5	—	$\mu\text{C}$

## Marking









$$R_G = 25 \, \Omega$$

$$V_{DD} = 90 \, \text{V}, L = 24.5 \, \text{mH}$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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